

What is claimed is:

1. A spiral inductor comprising:
 - a substrate;
 - a protruding portion which is formed on the top face of the substrate and the top of which serves as a dummy element for controlling a chemical mechanical polishing process; and
 - a conductive layer which is formed on the substrate so as to have a spiral shape and which serves as an induction element, wherein said protruding portion is formed in a region other than a region directly below said conductive layer.
2. A spiral inductor as set forth in claim 1, wherein the substrate is an SOI substrate, and
said protruding portion is formed of an SOI layer of said SOI substrate.
3. A spiral inductor as set forth in claim 2, wherein the substrate includes an N-type semiconductor layer.
4. A spiral inductor as set forth in claim 2, wherein the substrate includes a P-type semiconductor layer.
5. A spiral inductor comprising:
 - a substrate;
 - a protruding portion which is formed on the top face of the substrate and the top of which serves as a dummy element for controlling a chemical mechanical polishing process;
 - a conductive layer which is formed on the substrate so as to have a spiral shape and which serves as an induction element; and
 - a protective film which is formed between the substrate and said conductive layer and prevents silicidation of said protruding portion.
6. A spiral inductor as set forth in claim 5, wherein the substrate is an SOI substrate, and
said protruding portion is formed of an SOI layer of said

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SOI substrate.

7. A spiral inductor as set forth in claim 6, which further comprises an extracting wiring which is connected to said conductive layer.

8. A spiral inductor as set forth in claim 6, wherein the substrate includes an N-type semiconductor layer.

9. A spiral inductor as set forth in claim 6, wherein the substrate includes a P-type semiconductor layer.

10. A spiral inductor as set forth in claim 5, wherein said protruding portion is formed in a region other than a region directly below said conductive layer.

11. A spiral inductor as set forth in claim 10, wherein the substrate is an SOI substrate, and
said protruding portion is formed of an SOI layer of said SOI substrate.

12. A spiral inductor as set forth in claim 11, which further comprises an extracting wiring which is connected to said conductive layer.

13. A spiral inductor as set forth in claim 11, wherein the substrate includes an N-type semiconductor layer.

14. A spiral inductor as set forth in claim 11, wherein the substrate includes a P-type semiconductor layer.

15. A method for fabricating a semiconductor integrated circuit device comprising a substrate, and a spiral inductor which is formed on the substrate and which includes a spiral conductive layer serving as an induction element, said method comprising:

forming an element isolating groove in the surface of the substrate so that a protruding portion is formed in a region other

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than the region in which said conductive layer is formed, the top of said protruding portion serving as a dummy element for controlling a chemical mechanical polishing process.

16. A method for fabricating a semiconductor integrated circuit device as set forth in claim as set forth in claim 15, wherein the substrate is an SOI substrate, and

said protruding portion is formed of an SOI layer of said SOI substrate.

17. A method for fabricating a semiconductor integrated circuit device comprising a substrate, and a spiral inductor which is formed on the substrate so as to have a spiral shape and which includes a conductive layer serving as an induction element, said method comprising:

forming an element isolating groove in the surface of the substrate so that a protruding portion is formed, the top thereof serving as a dummy element for controlling a chemical mechanical polishing process;

depositing a protective film on the substrate;

selectively removing said protective film in a region other than a region in which said induction element is to be formed, by patterning using a photoresist; and

silicidating the surface of the substrate.

18. A method for fabricating a semiconductor integrated circuit device as set forth in claim 17, wherein the substrate is an SOI substrate, and

said protruding portion is formed of an SOI layer of said SOI substrate.

19. A method for fabricating a semiconductor integrated circuit device as set forth in claim 17, wherein said protruding portion is formed in a region other than a region directly below said conductive layer.

20. A method for fabricating a semiconductor integrated circuit

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device as set forth in claim as set forth in claim 19, wherein the substrate is an SOI substrate, and

said protruding portion is formed of an SOI layer of said SOI substrate.

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